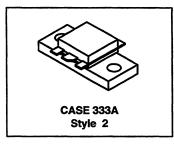
# The RF Line RF Power Transistor

The TP3064 is designed for 960 MHz mobile base stations in both analog and digital applications. It incorporates high value emitter ballast resistors, gold metallizations and offers a high degree of reliability and ruggedness. The TP3064 also features input and output matching networks and high impedances.

- Oxynitride Passivation
- Specified 26 Volts, 960 MHz Characteristics Output Power — 50 Watts Gain — 7.5 dB min Efficiency — 50% typ
- Class AB Operation

# **TP3064**

50 W, 960 MHz RF POWER TRANSISTOR NPN SILICON



#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCER	40	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	48	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	4	Vdc
Collector-Current — Continuous	Ic ·	10	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	145 0.8	Watts W/°C
Storage Temperature Range	T <sub>stg</sub>	- 65 to +150	.€
Operating Junction Temperature	TJ	200	.€

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (1)	R <sub>0</sub> JC	1.2	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ( $I_C = 60$ mA, $R_{BE} = 75 \Omega$ )	V(BR)CER	40	_		Vdc
Emitter Base Breakdown Voltage (IE = 15 mAdc)	V(BR)EBO	3.5	_		· Vdc
Collector-Emitter Breakdown Voltage (IC = 50 mAdc)	V(BR)CBO	48	_	_	Vdc
Collector-Emitter Leakage (V <sub>CE</sub> = 26 V, R <sub>BE</sub> = 75 Ω)	ICER	<u>-</u>	_	15	mA
N CHADACTERICTION		<u> </u>	<del></del>	L	

#### ON CHARACTERISTICS

DC Current Gain	hFE	15	 100	
(I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 10 Vdc)				

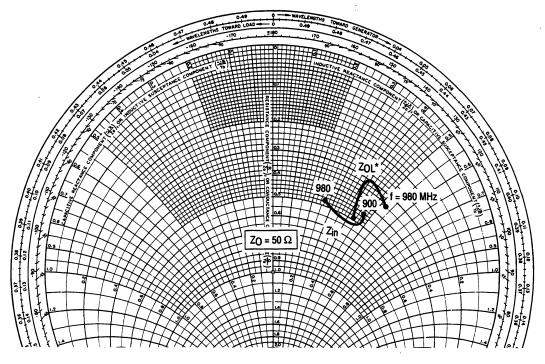
(1) Thermal resistance is determined under specified RF operating condition.



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# **ELECTRICAL CHARACTERISTICS** — **continued** ( $T_C = 25$ °C unless otherwise noted)

			200			
Characteristic	Symbol	Min	Тур	Max	Unit	
DYNAMIC CHARACTERISTICS (V <sub>CB</sub> = 26 V, f = 1 MHz)						
Output Capacitance (V <sub>CB</sub> = 26 V, I <sub>E</sub> = 0, f = 1 MHz)	C <sub>ob</sub>	_	60	_	pF	
FUNCTIONAL TESTS						
Common-Emitter Amplifier Gain (Pout = 50 W, I <sub>CQ</sub> = 200 mA, V <sub>CC</sub> = 26 V, f = 960 MHz)	G <sub>pa</sub>	7.5	8.5	-	dB	
Collector Efficiency (Pout = 50 W, V <sub>CC</sub> = 26 V, f = 960 MHz)	η	48	50		%	
Load Mismatch (Pout = 50 W, ICQ = 200 mA, VCC = 26 V, Load VSWR = 5:1, all phase angles at frequency of test)	Ψ	No Degradation in Output Power				

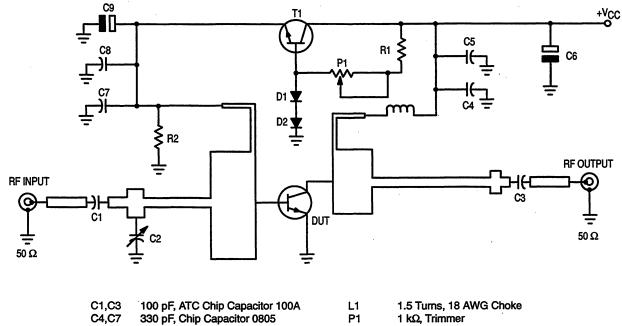


Output impedance with circuit tuned for maximum gain @  $P_{Out} = 50 \text{ W}$ ,  $V_{CE} = 26 \text{ V}$ 

f (MHz)	Z <sub>in</sub> (Ω)	Z <sub>OL</sub> * (Ω)
900	4.4 + j4.6	5 + j4.4
935	5.1 + j4.8	3 + j4.1
960	5.4 + j3.6	3.1 + j4.6
980	4.7 + j2.5	3.5 + j5

Z<sub>OL</sub>\* = Conjugate of optimum load impedance into which the device operates at a given output power, voltage, current and frequency.

Figure 1. Series Equivalent Input and Output Impedances



330 pF, Chip Capacitor 0805 1 kΩ, Trimmer P1 C5,C6 10 nF, Chip Capacitor 0805 R1 1 k $\Omega$ , Resistor C6 15 μF, 63 V, Capacitor R2 56 Ω, Resistor 0805 C9 100 μF, 16 V, Capacitor Diode, 1N4007 T1 Transistor, NPN Type, BD135 D1,D2

Figure 2. 960 MHz Test Circuit Schematic

## **TYPICAL CHARACTERISTICS**

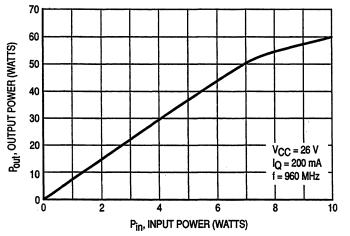


Figure 3. Output Power versus Input Power

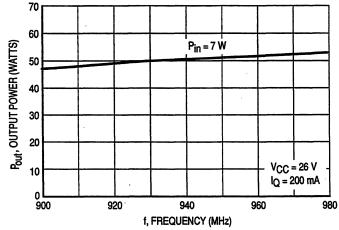
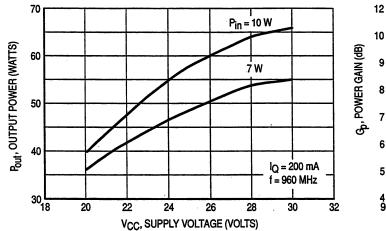


Figure 4. Output Power versus Frequency

## **TYPICAL CHARACTERISTICS**



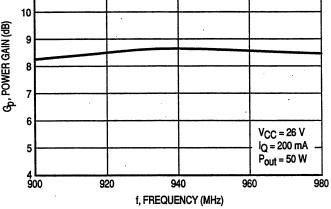


Figure 5. Output Power versus Supply Voltage

Figure 6. Broadband Amplifier

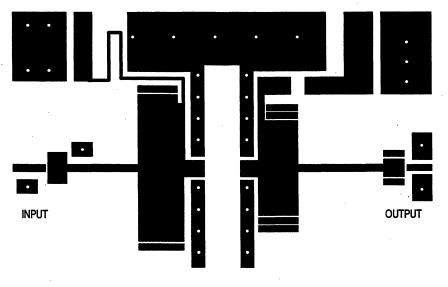
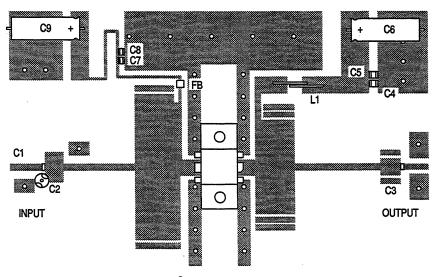


Figure 7. Photomaster

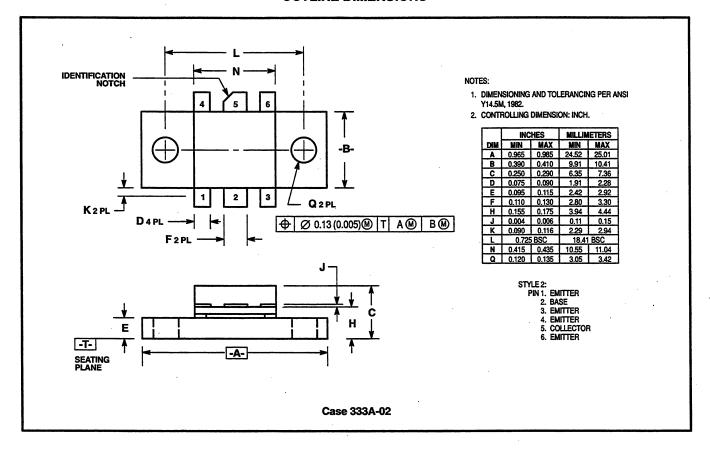
Scale 1:1

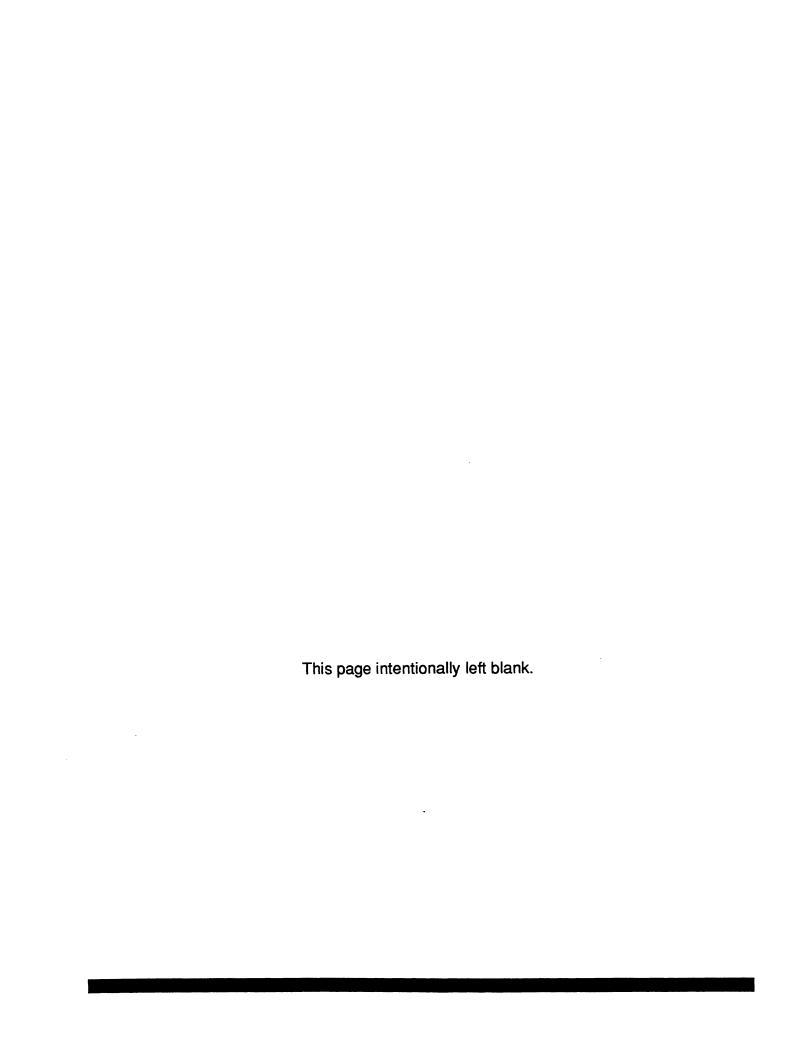


TEFLON® GLASS 1/50 INCH  $\epsilon_{\text{f}}$  = 2.55

Figure 8. 960 MHz Test Circuit Components View

## **OUTLINE DIMENSIONS**





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